

**Description**

The FDC604P is the high cell density trenched P-channel MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

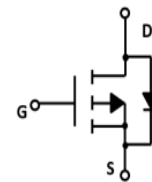
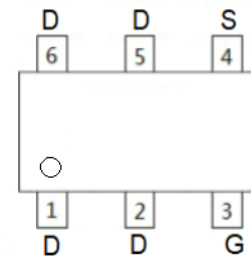
The FDC604P meet the RoHS and Green Product requirement with full function reliability approved.

- Super Low Gate Charge
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench
- technology

**Product Summary**

- $V_{DS} = -20V$   $I_D = -6.0A$
- $R_{DS(ON)} < 35m\Omega$  @  $V_{GS}=10V$
- $R_{DS(ON)} < 53 m\Omega$  @  $V_{GS} =4.5V$

**Pin Assignment**



**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-6.0	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.0	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-16	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	1.31	W
$P_D @ T_A=70^\circ C$	Total Power Dissipation <sup>3</sup>	0.84	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Electrical Characteristics** (T<sub>J</sub>=25°C unless otherwise specified)

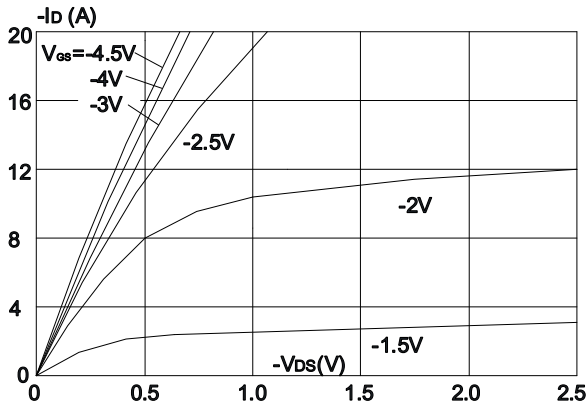
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> = -250μA	-20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -20V, V <sub>GS</sub> =0V,			-1	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V			±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.4	-0.7	-1.0	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note2</small>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4.1A		28	35	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3A	-	38	53	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = -10V, V <sub>GS</sub> =0V, f=1.0MHz		830		pF
C <sub>oss</sub>	Output Capacitance			132		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			85		pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = -10V, I <sub>D</sub> = -2A, V <sub>GS</sub> = -4.5V		8.8		nC
Q <sub>gs</sub>	Gate-Source Charge			1.4		nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge			1.9		nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> = -10V, I <sub>D</sub> = -3.3A, R <sub>G</sub> = 1Ω, V <sub>GEN</sub> = -4.5V		10		ns
t <sub>r</sub>	Turn-on Rise Time			32		ns
t <sub>d(off)</sub>	Turn-off Delay Time			50		ns
t <sub>f</sub>	Turn-off Fall Time			51		ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current				-5.0	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current				-16	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> = -4.1A			-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

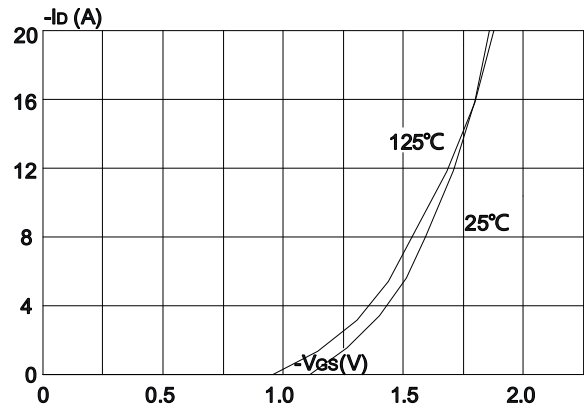
2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

### Typical Performance Characteristics

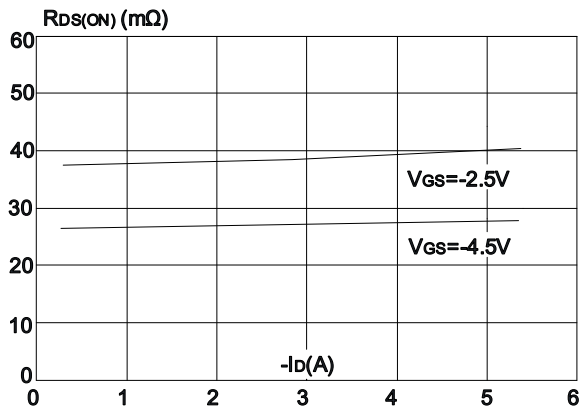
**Figure 1: Output Characteristics**



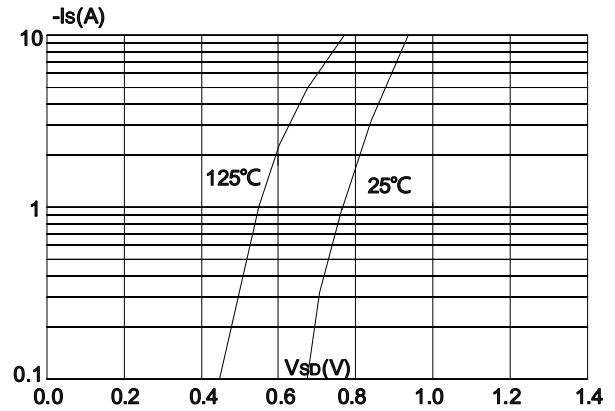
**Figure 2: Typical Transfer Characteristics**



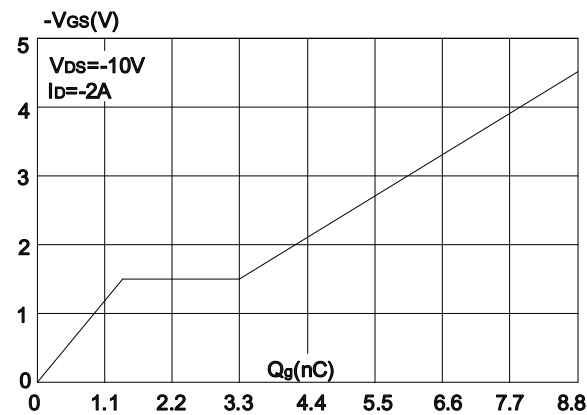
**Figure 3: On-resistance vs. Drain Current**



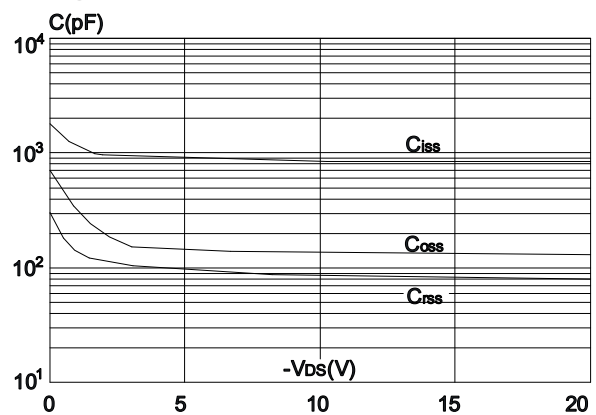
**Figure 4: Body Diode Characteristics**



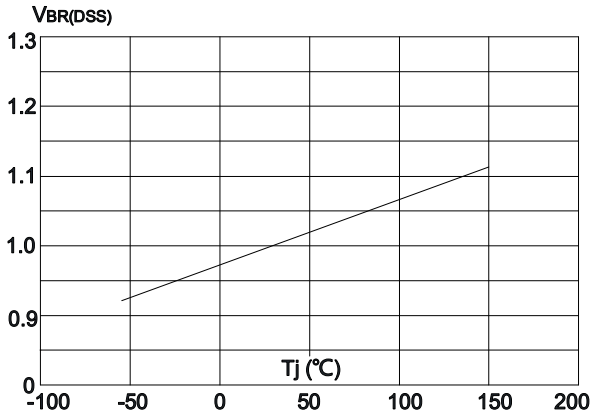
**Figure 5: Gate Charge Characteristics**



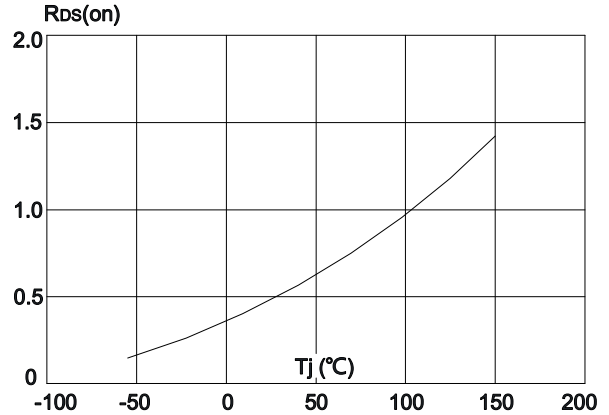
**Figure 6: Capacitance Characteristics**



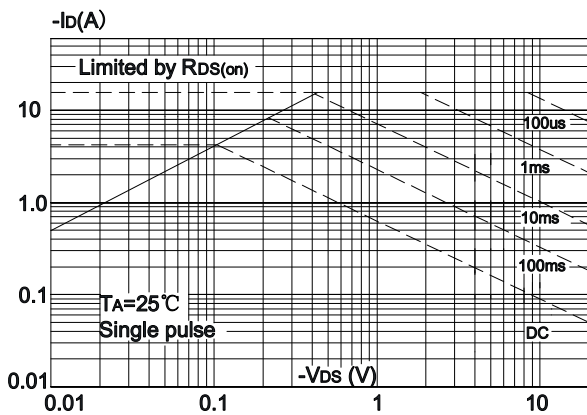
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



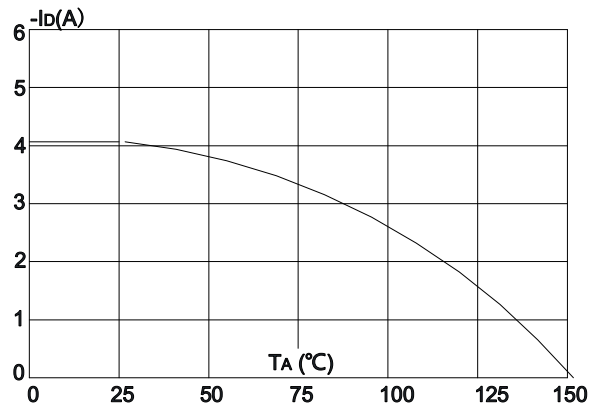
**Figure 8:** Normalized on Resistance vs. Junction Temperature



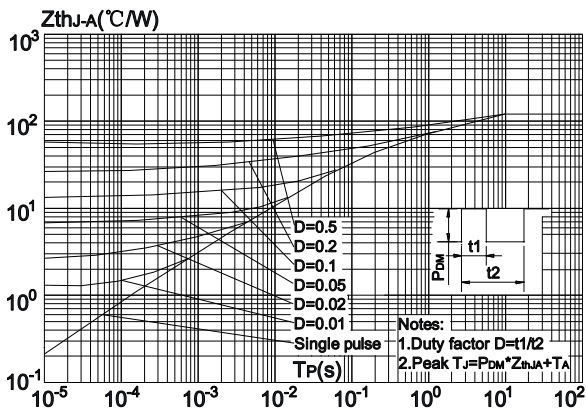
**Figure 9:** Maximum Safe Operating Area



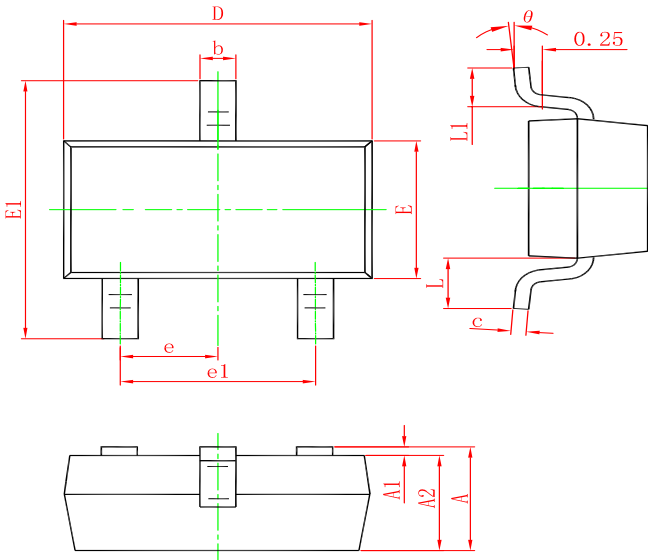
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	8°

Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FDC604P	SOT23-6	3000	Tape and reel

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